650V N-channel Super Junction MOSFET

MAIN CHARACTERISTICS

I_D	11A
V_{DS}	650V
R_{DSON}-typ(@V_{GS}=10V)	390mΩ(Typ:340mΩ)

FEATURES

- Ultra low RDS(on)
- Ultra low gate charge
- 100% UIS tested

APPLICATION

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply(UPS
- Power Factor Correction(PFC)

MECHANICAL DATA

- Case: TO-252/AD
- Mounting Position: Any
- Molded Plastic: UL Flammability Classification Rating 94V-0
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Solder bath temperature 275 maximum,10s per JESD 22-B106

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbol	Value	Unit

Ratin

Ratings and Characteristic Curves

Fig 7: Body Diode Characteristics

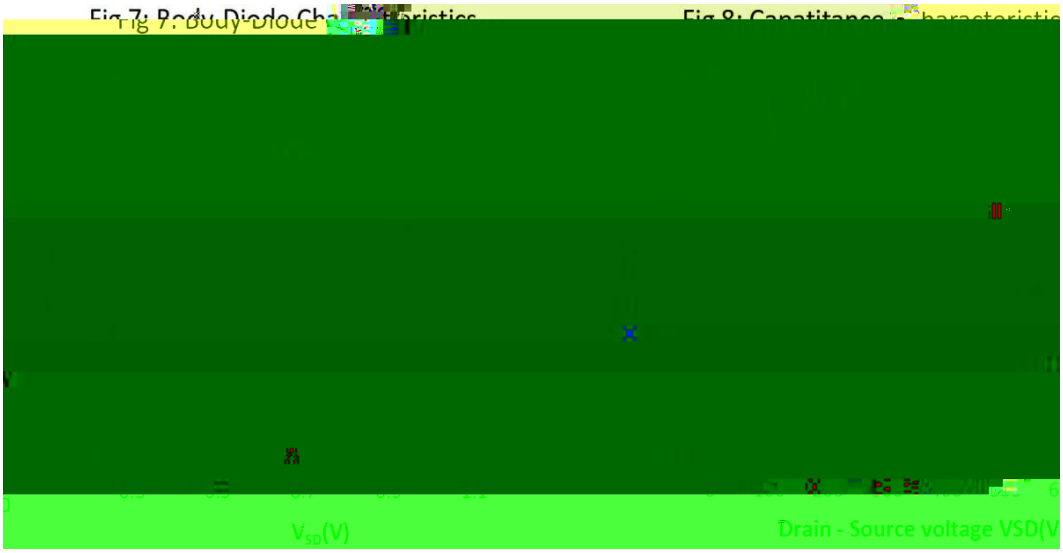

Fig 8: Capatitance Characteristic

Fig 9: Gate Quantity of electric charger vs. Gate Voltage

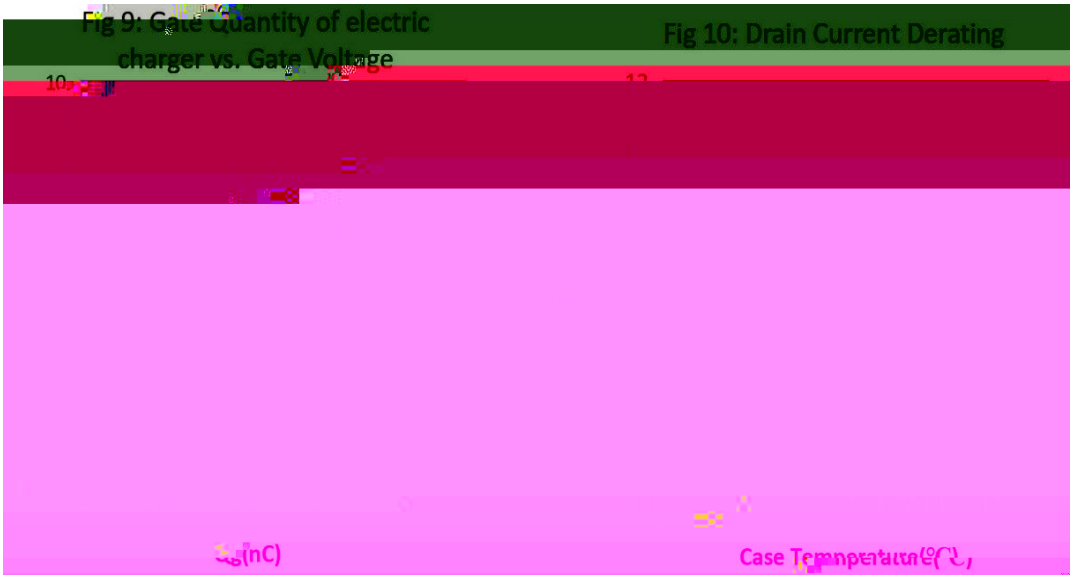

Fig 10: Drain Current Derating

Fig 11: Power Dissipation

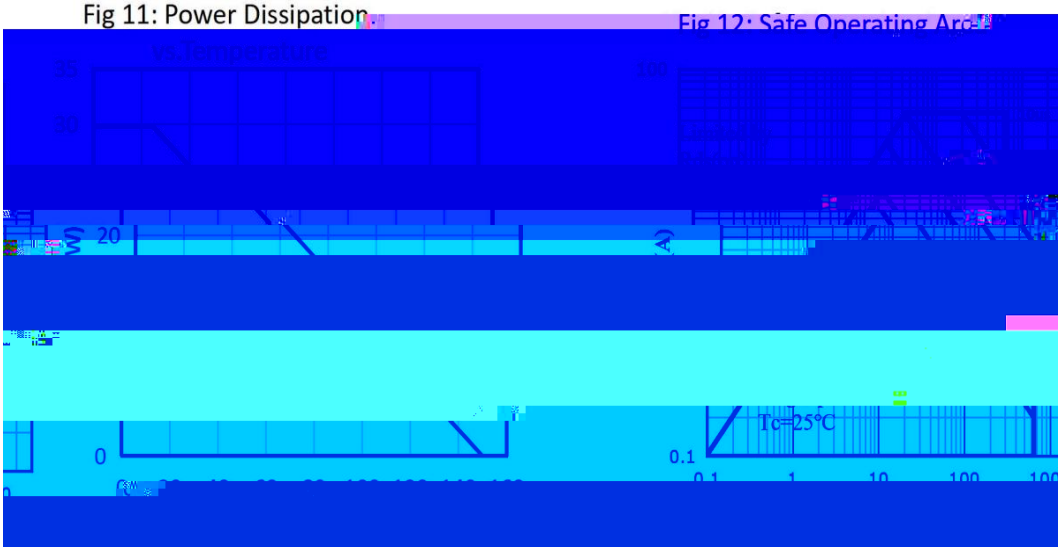

Fig 12: Safe Operating Area

YFW65R380AD

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